

# **SUT484J**

### Epitaxial planar PNP/NPN silicon transistor

## **Description**

• Complex type bipolar transistor

### **Feature**

- Small package save PCB area
- Reduce quantity of parts and mounting cost
- Both 2SA1980 chip and 2SC5343 chip in SOT-363 package

# Jy

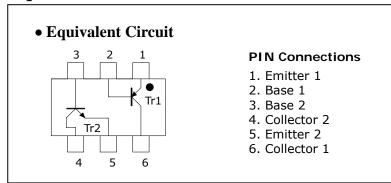
Package: SOT-363

## **Ordering Information**

Type NO.	Marking	Package Code
SUT484J	4X□	SOT-363

□: Year & Week Code

## **Equivalent circuit & PIN Connections**



## Absolute Maximum Ratings [Tr1, Tr2]

(Ta=25°C)

Characteristic	Symbol	Rating		Unit	
Characteristic		Tr1	Tr2	Omt	
Collector-base voltage	$V_{CBO}$	-50	60	V	
Collector-emitter voltage	$V_{CEO}$	-50	50	V	
Emitter-base voltage	$V_{EBO}$	-5	5	V	
Collector current	$I_{C}$	-150	150	mA	
Collector power dissipation	P <sub>C</sub> **	200		mW	
Junction temperature	T <sub>J</sub>	150		°C	
Storage temperature range	$T_{stg}$	-55~150		°C	

\*: Total rating

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# SUT484J

# **Electrical Characteristics** [Tr1]

(Ta=25°C)

Characteristic	Symbol Test Condition		Min.	Тур.	Max.	Unit
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	$I_C=-1$ mA, $I_B=0$	-50	-	1	V
Collector cut-off current	$I_{CBO}$	$V_{CB}$ =-50V, $I_{E}$ =0	-	-	-0.1	μΑ
Emitter cut-off current	$I_{EBO}$	$V_{EB}$ =-5V, $I_C$ =0	-	-	-0.1	μΑ
DC current gain	h <sub>FE</sub>	$V_{CE}$ =-6V, $I_{C}$ =-2mA	120	-	400	-
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-100mA, I <sub>B</sub> =-10mA	-	-	-0.3	V
Base-emitter voltage	$V_{BE}$	$V_{CE}$ =-6V, $I_{C}$ =-2mA	-	-0.65	ı	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-10mA	-	200	1	MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB}$ =-10V, $I_{E}$ =0, f=1MHz	-	4	-	pF

## **Electrical Characteristics** [Tr2]

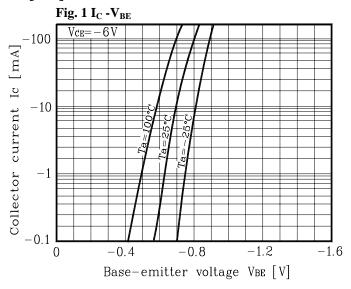
(Ta=25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	$I_C=1$ mA, $I_B=0$	50	ı	-	V
Collector cut-off current	$I_{CBO}$	V <sub>CB</sub> =60V, I <sub>E</sub> =0	ı	ı	0.1	μΑ
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V$ , $I_C=0$	ı	ı	0.1	μΑ
DC current gain	h <sub>FE</sub>	$V_{CE}$ =6V, $I_{C}$ =2mA	120	ı	400	-
Collector-emitter saturation voltage	$V_{CE(sat)}$	I <sub>C</sub> =100mA, I <sub>B</sub> =10mA	ı	ı	0.25	V
Base-emitter voltage	$V_{BE}$	$V_{CE}$ =6V, $I_{C}$ =2mA	ı	0.65	-	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA	ı	200	-	MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB}$ =10V, $I_{E}$ =0, f=1MHz	-	2	-	pF

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## **Electrical Characteristic Curves**

## [Tr1]



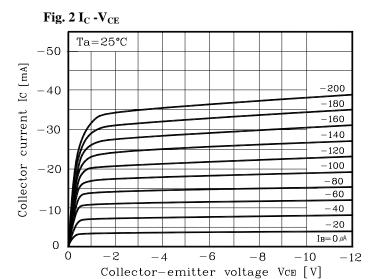
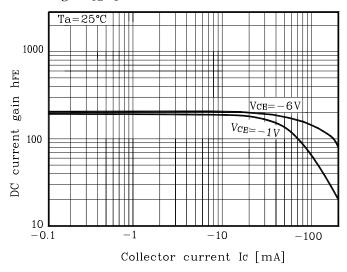
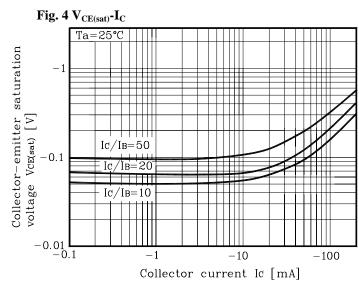
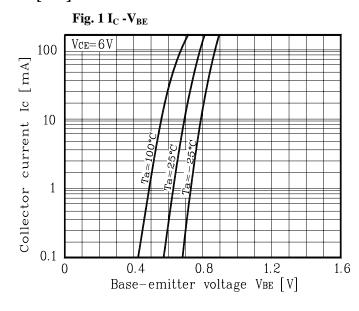


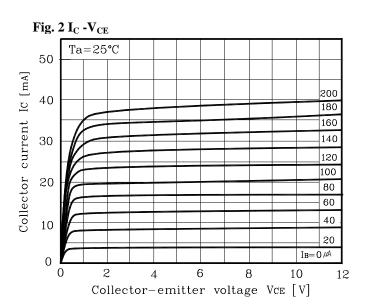
Fig. 3  $h_{FE}$ - $I_C$ 





[Tr2]





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## **Electrical Characteristic Curves**

Fig. 3  $h_{FE}$ - $I_C$ 

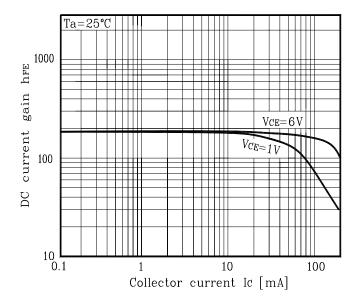
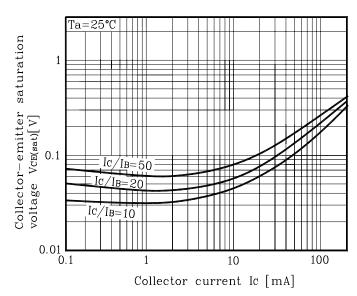
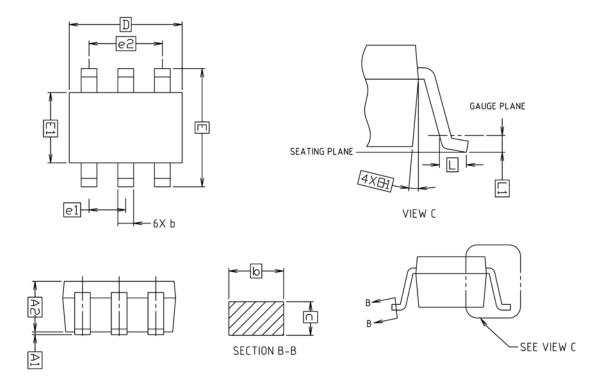


Fig. 4  $V_{\text{CE(sat)}}$ - $I_{\text{C}}$ 

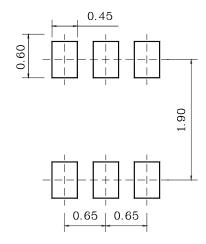


# **Outline Dimension**



	N.	NOTE		
SYMBOL	MINIMUM	NOMINAL	MAXIMUM	11012
A1	0.00	_	0.10	
A2	0.90	0.95	1.00	
b	0.25	_	0.40	
С	0.10	_	0.25	
D	1.90	2.00	2.10	
Ε	1.95	2.10	2.25	
E1	1.15	1.25	1.35	
e1				
e2				
L	0.25	_	_	
L1				

## \* Recommend PCB solder land [Unit: mm]



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